

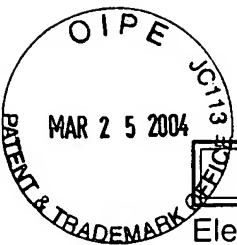


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Electronic Patent Application Submission
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EFS ID: 57874
Application ID: 10722792 
Title of Invention: Method of Fabricating a High-Voltage Transistor With A Multi-Layered Extended Drain Structure
First Named Inventor: Donald Disney
Domestic/Foreign Application: Domestic Application
Filing Date: 2003-11-25
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Confirmation number: 7244
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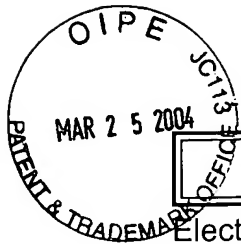
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TRANSMITTAL

Electronic Version v1.1
Stylesheet Version v1.1.0

Title of Invention	Method of Fabricating a High-Voltage Transistor With A Multi-Layered Extended Drain Structure									
<p>Application Number: 10/722792 </p> <p>Date: 2003-11-25</p> <p>First Named Applicant: Donald Ray Disney</p> <p>Confirmation Number: 7244</p> <p>Attorney Docket Number: 03692.P059DC</p>										
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<table border="1"><thead><tr><th>Submitted by:</th><th>Elec. Sign.</th><th>Sign. Capacity</th></tr></thead><tbody><tr><td>Bradley John Berezna Registered Number: 33,474</td><td>BJB</td><td>Attorney</td></tr></tbody></table>			Submitted by:	Elec. Sign.	Sign. Capacity	Bradley John Berezna Registered Number: 33,474	BJB	Attorney		
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Bradley John Berezna Registered Number: 33,474	BJB	Attorney								
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	us-ids.dtd									
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Comments										



ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of
Invention

Method of Fabricating a High-Voltage Transistor With A
Multi-Layered Extended Drain Structure

Application Number: 10/722792



Confirmation Number: 7244

First Named Applicant: Donald Disney

Attorney Docket Number: 03692.P059DC

Art Unit: 2818

Examiner: David Nhu

Search string: (6184555 or 6462377 or 6127703 or 5306656
or 6525372 or 6468847 or 5973360 or 5637898
or 5665994 or 4929987 or 4531173 or 6573558
or 6555873 or 6509220 or 6667213 or 6635544
or 6365932 or 4626789 or 6294818 or 5760440
or 6049108 or 5821144 or 4738936 or 5869875
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or 5237193 or 5368136 or 5313082 or 5068700
or 5258636 or 20020175351 or 20020056884 or
20010015459).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

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Signature

Examiner Name	Date